DS90LV001 800 Mbps LVDS Buffer



DS90LV001 800 Mbps LVDS Buffer

General Description

The DS90LV001 LVDS-LVDS Buffer takes an LVDS input signal and provides an LVDS output signal. In many large systems, signals are distributed across backplanes, and one of the limiting factors for system speed is the "stub length" or the distance between the transmission line and the unterminated receivers on individual cards. Although it is generally recognized that this distance should be as short as possible to maximize system performance, real-world packaging concerns often make it difficult to make the stubs as short as the designer would like.

The DS90LV001, available in the LLP (Leadless Leadframe Package) package, will allow the receiver to be placed very close to the main transmission line, thus improving system performance.

A wide input dynamic range will allow the DS90LV001 to receive differential signals from LVPECL as well as LVDS sources. This will allow the device to also fill the role of an LVPECL-LVDS translator. An output enable pin is provided, which allows the user to place the LVDS output in TRI-STATE.

The DS90LV001 is offered in two package options, an 8 pin LLP and SOIC.

Features

- Single +3.3 V Supply
- LVDS receiver inputs accept LVPECL signals
- TRI-STATE outputs
- Receiver input threshold < ±100 mV</p>
- Fast propagation delay of 1.4 ns (typ)
- Low jitter 800 Mbps fully differential data path
- 100 ps (typ) of pk-pk jitter with PRBS = 2²³-1 data pattern at 800 Mbps
- Compatible with ANSI/TIA/EIA-644-A LVDS standard
- 8 pin SOIC and space saving (70%) LLP package
- Industrial Temperature Range

Top View GND ΕN OUT-IN-7 OUT+ IN+ 6 NC 5 V_{CC} Order Number DS90LV001TM, DS90LV001TLD See NS Package Number M08A, LDA08A Block Diagram IN-OUT-IN+ OUT+ FΝ 10133802

Connection Diagram

Absolute Maximum Ratings (Note 1)

If Military/Aerospace specified devices are required, please contact the National Semiconductor Sales Office/ Distributors for availability and specifications.

Supply Voltage (V _{CC})	-0.3V to +4V
LVCMOS/LVTTL Input Voltage (EN)	–0.3V to (V _{CC} + 0.3V)
LVDS Receiver Input Voltage (IN +, IN–)	-0.3V to +4V
LVDS Driver Output Voltage (OUT +, OUT–)	-0.3V to +4V
LVDS Output Short Circuit Current	Continuous
Junction Temperature	+150°C
Storage Temperature Range	-65°C to +150°C
Lead Temperature Range	
Soldering (4 sec.)	+260°C

Maximum Package Power Dissi	pation at 25°C
M Package	726 mW
Derate M Package	5.8 mW/°C above +25°C
LDA Package	2.44 W
Derate LDA Package	19.49 mW/°C above +25°C
ESD Ratings	
(HBM, 1.5kΩ, 100pF)	≥2.5kV
(EIAJ, 0Ω, 200pF)	≥250V

Recommended Operating Conditions

	Min	Тур	Мах	Units	
Supply Voltage (V _{CC})	3.0	3.3	3.6	V	
Receiver Input Voltage	0		V_{cc}	V	
Operating Free Air Temperature	-40	+25	+85	°C	
remperature					

Electrical Characteristics

Over recommended operating supply and temperature ranges unless otherwise specified. (Notes 2, 3)

Symbol	Parameter	Conditions	Min	Тур	Max	Units
LVCMOS	S/LVTTL DC SPECIFICATIONS (EN)			•		
V _{IH}	High Level Input Voltage		2.0		V _{cc}	V
V _{IL}	Low Level Input Voltage		GND		0.8	V
I _{IH}	High Level Input Current	$V_{IN} = 3.6V \text{ or } 2.0V, V_{CC} = 3.6V$		+7	+20	μA
I _{IL}	Low Level Input Current	$V_{IN} = GND \text{ or } 0.8V, V_{CC} = 3.6V$		±1	±10	μA
V _{CL}	Input Clamp Voltage	$I_{CL} = -18 \text{ mA}$		-0.6	-1.5	V
LVDS O	UTPUT DC SPECIFICATIONS (OUT)	•	·		•	
V _{OD}	Differential Output Voltage	R _L = 100Ω	250	325	450	mV
ΔV_{OD}	Change in Magnitude of V _{OD} for Complimentary Output States	Figure 1 and Figure 2			20	mV
V _{os}	Offset Voltage	R _L = 100Ω	1.080	1.19	1.375	V
ΔV _{OS}	Change in Magnitude of V _{OS} for Complimentary Output States	Figure 1			20	mV
I _{oz}	Output TRI-STATE Current	$EN = 0V, V_{OUT} = V_{CC} \text{ or } GND$		±1	±10	μA
I _{OFF}	Power-Off Leakage Current	$V_{CC} = 0V, V_{OUT} = 3.6V \text{ or GND}$		±1	±10	μA
l _{os}	Output Short Circuit Current (Note 4)	$EN = V_{CC}, V_{OUT+} and V_{OUT-} = 0V$		-16	-24	mA
I _{OSD}	Differential Output Short Circuit Current (Note 4)	$EN = V_{CC}, V_{OD} = 0V$		-7	-12	mA
LVDS RI	ECEIVER DC SPECIFICATIONS (IN)	÷	·	•		
V _{TH}	Differential Input High Threshold	V_{CM} = +0.05V, +1.2V or +3.25V		0	+100	mV
V _{TL}	Differential Input Low Threshold		-100	0		mV
V _{CMR}	Common Mode Voltage Range	$V_{ID} = 100 \text{mV}, V_{CC} = 3.3 \text{V}$	0.05		3.25	V
I _{IN}	Input Current	$V_{IN} = +3.0V$ $V_{CC} = 3.6V \text{ or } 0V$		±1	±10	μA
		V _{IN} = 0V		±1	±10	μA
ΔI _{IN}	Change in Magnitude of I _{IN}	$V_{IN} = +3.0V$ $V_{CC} = 3.6V \text{ or } 0V$		1	6	μA
		$V_{IN} = 0V$		1	6	μA
SUPPLY	CURRENT	· · ·	·			8
I _{CCD}	Total Supply Current	$EN = V_{CC}, R_{L} = 100\Omega, C_{L} = 5 \text{ pF}$		47	70	mA
I _{ccz}	TRI-STATE Supply Current	EN = 0V		22	35	mA

DS90LV001

AC Electrical Characteristics

Over recommended operating supply and temperature ranges unless otherwise specified. (Note 3)

Symbol	Parameter	Conditions	Min	Тур	Max	Units
t _{PHLD}	Differential Propagation Delay High to Low	$R_{L} = 100\Omega, C_{L} = 5pF$	1.0	1.4	2.0	ns
t _{PLHD}	Differential Propagation Delay Low to High	Figure 3 and Figure 4	1.0	1.4	2.0	ns
t _{SKD1}	Pulse Skew It _{PLHD} – t _{PHLD} I (Notes 5, 6)			20	200	ps
t _{SKD3}	Part to Part Skew (Notes 5, 7)			0	60	ps
t _{SKD4}	Part to Part Skew (Notes 5, 8)				400	ps
t _{LHT}	Rise Time (Note 5)	$R_{L} = 100\Omega, C_{L} = 5pF$	200	320	450	ps
t _{HLT}	Fall Time (Note 5)	Figure 3 and Figure 5	200	310	450	ps
t _{PHZ}	Disable Time (Active High to Z)	$R_{L} = 100\Omega, C_{L} = 5pF$		3	25	ns
t _{PLZ}	Disable Time (Active Low to Z)	Figure 6 and Figure 7		3	25	ns
t _{PZH}	Enable Time (Z to Active High)			25	45	ns
t _{PZL}	Enable Time (Z to Active Low)			25	45	ns
t _{DJ}	LVDS Data Jitter, Deterministic (Peak-to-Peak) (Note 9)	V _{ID} = 300mV; PRBS = 2 ²³ - 1 data; V _{CM} = 1.2V at 800Mbps (NRZ)		100	135	ps
t _{RJ}	LVDS Clock Jitter, Random (Note 9)	V_{ID} = 300mV; V_{CM} = 1.2V at 400MHz clock		2.2	3.5	ps

Note 1: "Absolute Maximum Ratings" are those values beyond which the safety of the device cannot be guaranteed. They are not meant to imply that the device should be operated at these limits. The table of "Electrical Characteristics" specifies conditions of device operation.

Note 2: Current into device pins is defined as positive. Current out of device pins is defined as negative. All voltages are referenced to ground except V_{OD} and ΔV_{OD} .

Note 3: All typical are given for V_{CC} = +3.3V and T_A = +25^{\circ}C, unless otherwise stated.

Note 4: Output short circuit current (I_{OS}) is specified as magnitude only, minus sign indicates direction only.

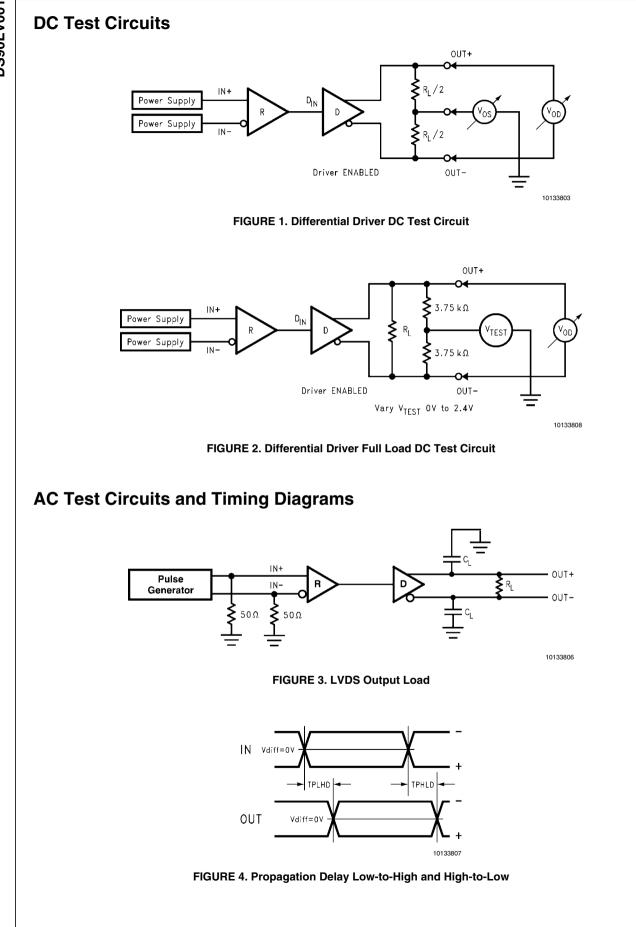
Note 5: The parameters are guaranteed by design. The limits are based on statistical analysis of the device performance over the PVT (process, voltage and temperature) range.

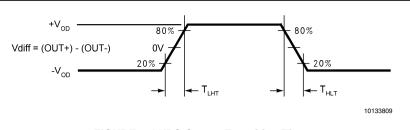
Note 6: t_{SKD1}, lt_{PLHD} - t_{PHLD}I, is the magnitude difference in differential propagation delay time between the positive going edge and the negative going edge of the same channel.

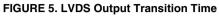
Note 7: t_{SKD3}, Part to Part Skew, is defined as the difference between the minimum and maximum specified differential propagation delays. This specification applies to devices at the same V_{CC} and within 5°C of each other within the operating temperature range.

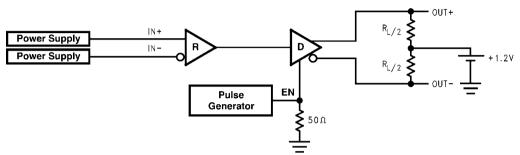
Note 8: t_{SKD4}, Part to Part Skew, is the differential channel-to- channel skew of any event between devices. This specification applies to devices over recommended operating temperature and voltage ranges, and across process distribution. t_{SKD4} is defined as IMax – MinI differential propagation delay.

Note 9: The parameters are guaranteed by design. The limits are based on statistical analysis of the device performance over the PVT range with the following test equipment setup: HP8133A (pattern pulse generator), 5 feet of RG142B cable with DUT test board and HP83480A (digital scope mainframe) with HP83484A (50GHz scope module). The HP8133A with RG142B cable exhibit a $t_{DJ} = 21$ ps and $t_{RJ} = 1.8$ ps.









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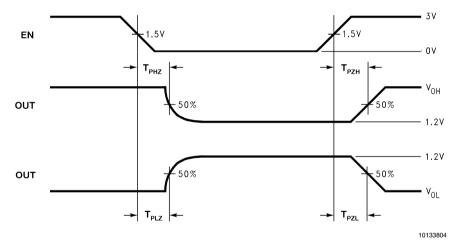


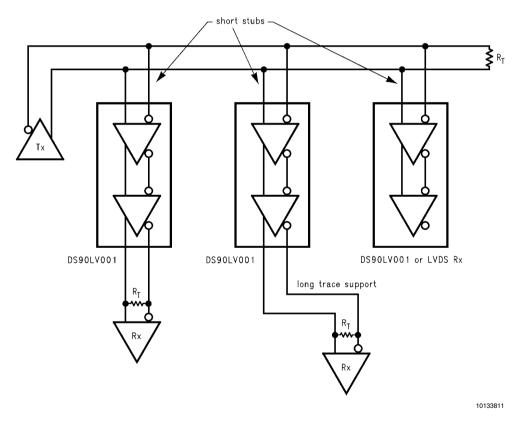
FIGURE 7. Output active to TRI-STATE and TRI-STATE to active output time

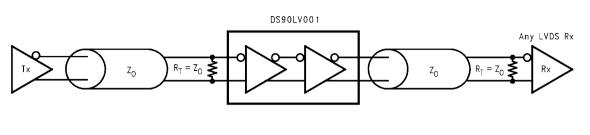
DS90LV001 Pin Descriptions (SOIC and LLP)

Pin Name	Pin #	Input/Output	Description
GND	1	Р	Ground
IN –	2	I	Inverting receiver LVDS input pin
IN+	3	I	Non-inverting receiver LVDS input pin
NC	4		No Connect
V _{CC}	5	Р	Power Supply, $3.3V \pm 0.3V$.
OUT+	6	0	Non-inverting driver LVDS output pin
OUT -	7	0	Inverting driver LVDS output pin
EN	8	I	Enable pin. When EN is LOW, the driver is disabled and the LVDS outputs are in TRI-STATE. When EN is HIGH, the driver is enabled. LVCMOS/LVTTL levels.
DAP	NA	NA	Die Attach Pad or DAP (LLP Package only). The DAP is NOT connected to the device GND nor any other pin. It is still recommended to connect the DAP to a GND plane of a PCB for enhenced heat dissipation.

Typical Applications

Backplane Stub-Hider Application





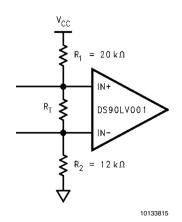
Application Information

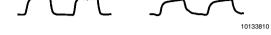
MODE OF OPERATION

The DS90LV001 can be used as a "stub-hider." In many systems, signals are distributed across backplanes, and one of the limiting factors for system speed is the "stub length" or the distance between the transmission line and the unterminated receivers on the individual cards. Although it is generally recognized that this distance should be as short as possible to maximize system performance, real-world packaging concerns and PCB designs often make it difficult to make the stubs as short as the designer would like. The DS90LV001, available in the LLP (Leadless Leadframe Package) package. can improve system performance by allowing the receiver to be placed very close to the main transmission line either on the backplane itself or very close to the connector on the card. Longer traces to the LVDS receiver may be placed after the DS90LV001. This very small LLP package is a 75% space savings over the SOIC package.

INPUT FAILSAFE

The receiver inputs of the DS90LV001 do not have internal failsafe biasing. For point-to-point and multidrop applications with a single source, failsafe biasing may not be required. When the driver is off, the link is in-active. If failsafe biasing is required, this can be accomplished with external high value resistors. Using the equations in the LVDS Owner's Manual Chapter 4, the IN+ should be pull to V_{CC} (3.3V) with 20k Ω and the IN- should be pull to GND with 12k Ω . This provides a slight positive differential bias, and sets a known HIGH state on the link with a minimum amount of distortion.





DS90LV001

PCB LAYOUT AND POWER SYSTEM BYPASS

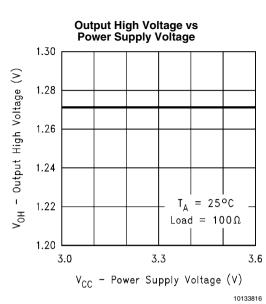
Circuit board layout and stack-up for the DS90LV001 should be designed to provide noise-free power to the device. Good layout practice also will separate high frequency or high level inputs and outputs to minimize unwanted stray noise pickup, feedback and interference. Power system performance may be greatly improved by using thin dielectrics (4 to 10 mils) for power/ground sandwiches. This increases the intrinsic capacitance of the PCB power system which improves power supply filtering, especially at high frequencies, and makes the value and placement of external bypass capacitors less critical. External bypass capacitors should include both RF ceramic and tantalum electrolytic types. RF capacitors may use values in the range 0.01 µF to 0.1 µF. Tantalum capacitors may be in the range 2.2 µF to 10 µF. Voltage rating for tantalum capacitors should be at least 5X the power supply voltage being used. It is recommended practice to use two vias at each power pin of the DS90LV001 as well as all RF bypass capacitor terminals. Dual vias reduce the interconnect inductance by up to half, thereby reducing interconnect inductance and extending the effective frequency range of the bypass components.

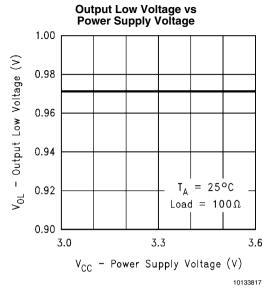
The outer layers of the PCB may be flooded with additional ground plane. These planes will improve shielding and isolation as well as increase the intrinsic capacitance of the power supply plane system. Naturally, to be effective, these planes must be tied to the ground supply plane at frequent intervals with vias. Frequent via placement also improves signal integrity on signal transmission lines by providing short paths for image currents which reduces signal distortion. The planes should be pulled back from all transmission lines and component mounting pads a distance equal to the width of the widest transmission line or the thickness of the dielectric separating the transmission line from the internal power or ground plane(s) whichever is greater. Doing so minimizes effects on transmission line impedances and reduces unwanted parasitic capacitances at component mounting pads.

There are more common practices which should be followed when designing PCBs for LVDS signaling. Please see application note AN-1108 for guidelines. In addition, application note AN-1187 has additional information specifically related to LLP recommendations.

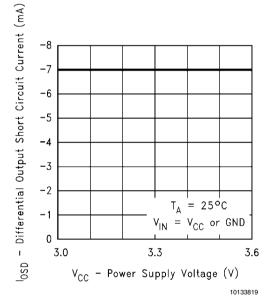
Typical Performance Curves



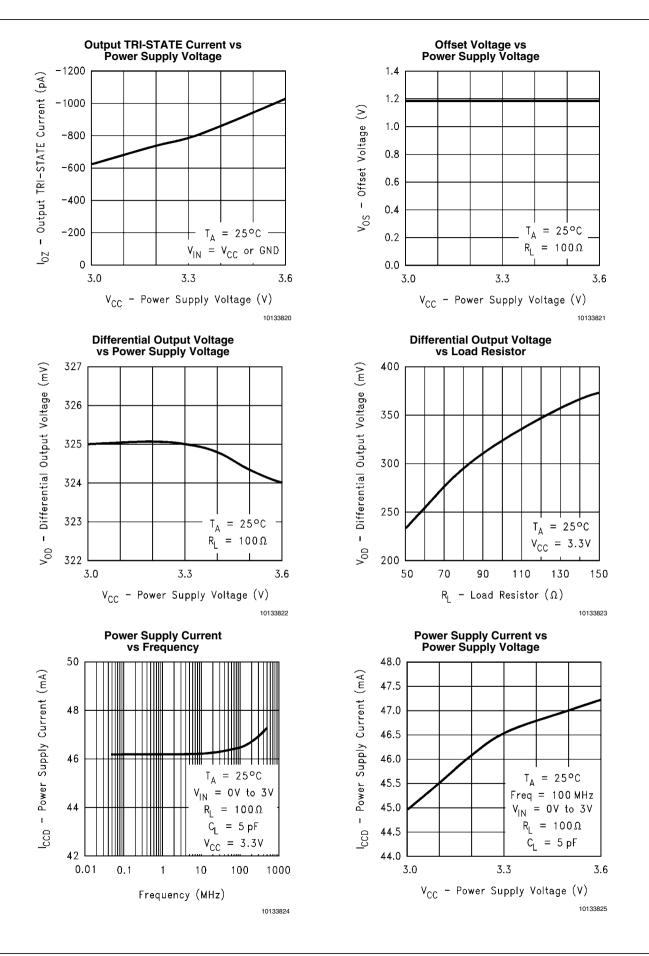




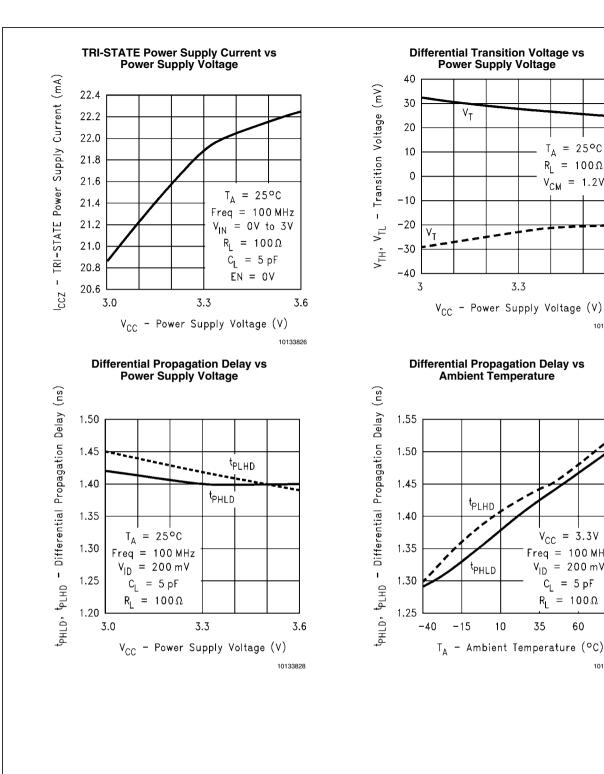
Differential Output Short Circuit Current vs Power Supply Voltage



Output Short Circuit Current vs Power Supply Voltage - Output Short Circuit Current (mA) -16.0 -15.8 -15.6 -15.4 $T_{A} = 25^{\circ}C$ -15.2 $V_{IN} = V_{CC}$ or GND los -15.0 3.0 3.3 3.6 V_{CC} - Power Supply Voltage (V) 10133818







 T_A

 R_{L}

= 25°C

= 100Ω

3.6

10133827

 $V_{CM} = 1.2V$

 $V_{CC} = 3.3V$

Freq = 100 MHz

 $= 200 \, mV$

= 5 pF

= 100Ω

60

85

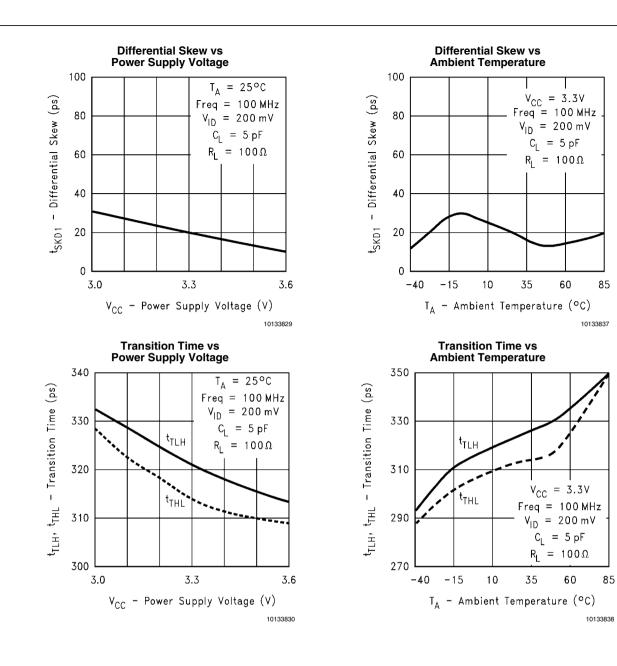
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 v_{ID}

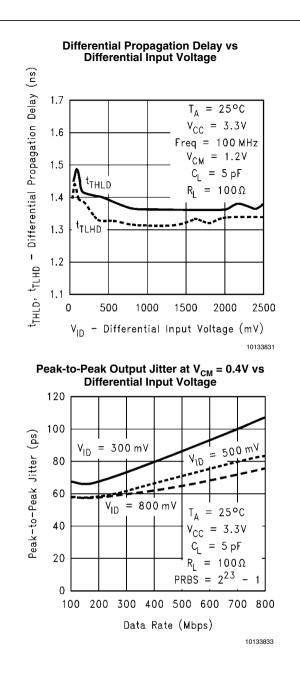
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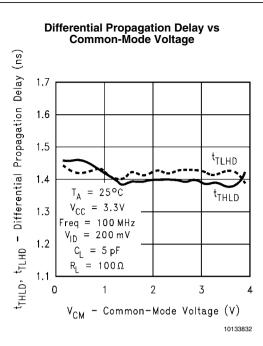
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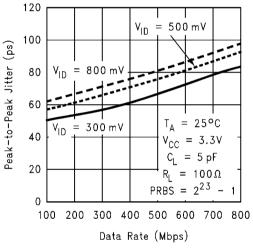




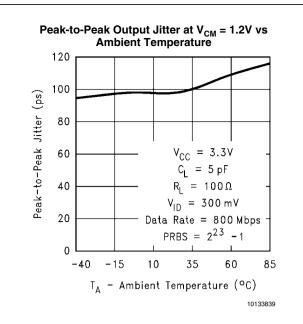


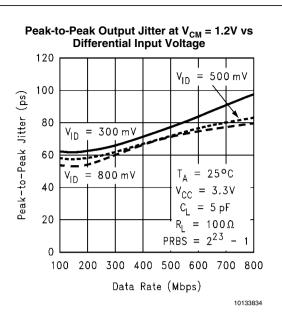


Peak-to-Peak Output Jitter at V_{CM} = 2.9V vs Differential Input Voltage

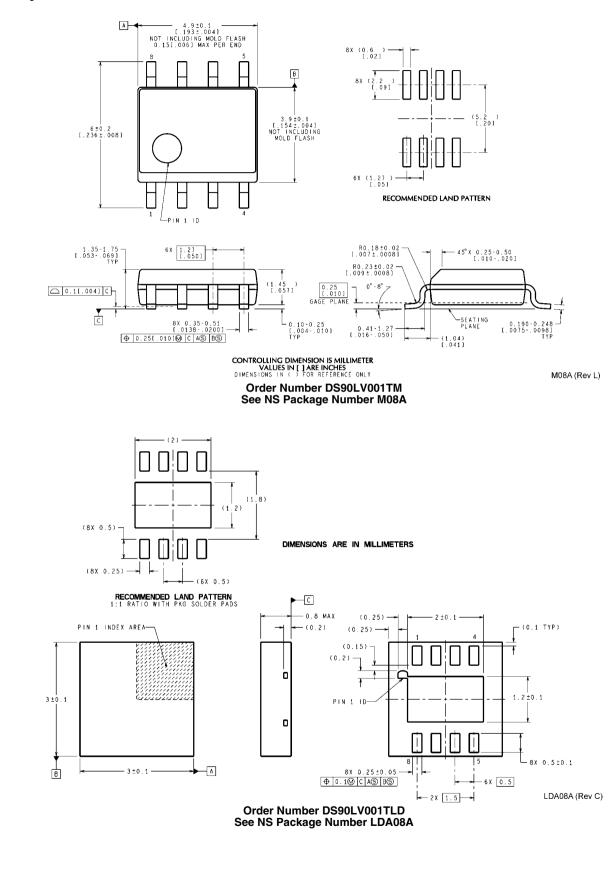


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Physical Dimensions inches (millimeters) unless otherwise noted



Notes

Notes

Pr	oducts	Design Support		
Amplifiers	www.national.com/amplifiers	WEBENCH	www.national.com/webench	
Audio	www.national.com/audio	Analog University	www.national.com/AU	
Clock Conditioners	www.national.com/timing	App Notes	www.national.com/appnotes	
Data Converters	www.national.com/adc	Distributors	www.national.com/contacts	
Displays	www.national.com/displays	Green Compliance	www.national.com/quality/green	
Ethernet	www.national.com/ethernet	Packaging	www.national.com/packaging	
Interface	www.national.com/interface	Quality and Reliability	www.national.com/quality	
LVDS	www.national.com/lvds	Reference Designs	www.national.com/refdesigns	
Power Management	www.national.com/power	Feedback	www.national.com/feedback	
Switching Regulators	www.national.com/switchers			
LDOs	www.national.com/ldo			
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